

Abstract

The present invention relates to a method for treating porous graphite substrates, in which at least one film is provided, the at least one film comprising silicon particles and at least one binding agent, the at least one film is applied to at least one surface of a porous graphite substrate, and the at least one applied film is subjected to at least one heat treatment in which the silicon particles melt into a melt which at least partially infiltrates into pores of the graphite substrate, wherein silicon contained in the melt is at least partially converted into silicon carbide. In addition, the present invention also relates to a treated substrate and its use.

[Figure 1]